

Attorney Docket No.: 24061.27
Customer No. 27683

**INVENTOR'S DECLARATION FOR
PATENT APPLICATION**

As the below named inventors, we hereby declare that:

Our residence, post office address and citizenship are as stated below next to our names;

We believe we are the original, first and sole joint inventors of the subject matter which is claimed and for which a patent is sought on the invention entitled

**ELECTROSTATIC DISCHARGE PROTECTION STRUCTURE
FOR DEEP SUB-MICRON GATE OXIDE**

the specification of which: (check one)

 X is attached hereto.

_____ was filed on _____
under Attorney's Docket Number _____
as Application Serial No. _____
and was amended on _____ (if applicable).

We hereby state that we have reviewed and understand the contents of the above identified specification, including the claims, as amended by any amendment referred to above.

We acknowledge the duty to disclose information which is material to the patentability of this application in accordance with 37 CFR 1.56, including for continuation-in-part applications, material information which became available between the filing date of the prior application and the national or PCT international filing date of the continuation-in-part application.

We hereby declare that all statements made herein of our own knowledge are true and that all statements made on information and belief are believed to be true; and further that these statements were made with the knowledge that willful false statements and the like so made are punishable by fine or imprisonment, or both, under 18 U.S.C 1001 and that such willful false statements may jeopardize the validity of the application or any patent issued thereon.

We hereby claim the benefit under Title 35, United States Code, § 119(e) of any United States provisional application(s) listed below.

(Application Number)

(Filing Date)

We hereby claim foreign priority benefits under 35 U.S.C. 119(a)-(d) or (f), or 365(b) of any foreign applications for patent, inventor's or plant breeder's rights certificate(s), or 365(a) of any PCT international application which designated at least one country other than the United States of America, listed below, any foreign application for patent, inventor's or plant breeder's rights certificate(s), or any PCT

Attorney Docket No..24061.27
Customer No. 27683

international application having a filing date before that of the application on which priority is claimed.

Prior Foreign Application Number(s)	Country	Foreign Filing Date (MM/DD/YYYY)	Priority Claimed

FULL NAME OF INVENTOR: Yi-Hsun Wu

INVENTOR'S SIGNATURE: Yi Hsun Wu DATED: 09/08/2003

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CITIZENSHIP: ^{Taiwan}~~China~~ Republic of China

POST OFFICE ADDRESS:

FULL NAME OF INVENTOR: Jian-Hsin Lee

INVENTOR'S SIGNATURE: Jian Hsin Lee DATED: 9.8/03

RESIDENCE: No. 11, Pao-San Rd., Hsin-chu, Taiwan.

CITIZENSHIP: ~~China~~ Republic of China

POST OFFICE ADDRESS:

FULL NAME OF INVENTOR: Tongchern Ong

INVENTOR'S SIGNATURE: Tong Chern Ong DATED: 9/15/03

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CITIZENSHIP: ~~China~~ Republic of China

Taiwan, R.O.C.

POST OFFICE ADDRESS:

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of:	§	Attorney Docket No.: 24061.27
Wu, et al.	§	TSMC2002-1168
	§	
Serial No.: Unknown	§	Customer No. 27683
	§	
Filed: Herewith	§	Group Art Unit: Unknown
	§	
For: ELECTROSTATIC DISCHARGE	§	Examiner: n/a
PROTECTION STRUCTURE FOR	§	
DEEP SUB-MICRON GATE OXIDE	§	

Commissioner for Patents
Washington, D.C. 20231

POWER OF ATTORNEY FOR PATENT APPLICATION

As a representative of the Assignee, Taiwan Semiconductor Manufacturing Company, Ltd., I hereby appoint the following attorneys and/or agents to prosecute this application and transact all business in the Patent and Trademark Office connected therewith.

David L. McCombs (Reg. No. 32,271); Jeffrey M. Becker (Reg. No. 35,442); James R. Bell (Reg. No. 26,528); Timothy F. Bliss (Reg. No. 50,925); Randall C. Brown (Reg. No. 31,213); Randall E. Colson (Reg. No. 40,566); Michael A. Davis, Jr. (Reg. No. 35,488); Andrew S. Ehmke (Reg. No. 50,271); Priscilla Ferguson (Reg. No. 42,531); Sarah T. Harris (Reg. No. 35,891); William E. Hickman (Reg. No. 46,771); Rita M. Irani (Reg. No. 31,028); Warren B. Kice (Reg. No. 22,732); J. Andrew Lowes (Reg. No. 40,706); Todd Mattingly (Reg. No. 40,298); John Montgomery (Reg. No. 31,124); Julie Nickols (Reg. No. 50,826); Gloria Norberg (Reg. No. 36,706); David M. O'Dell (Reg. No. 42,044); Richard V. Wells (Reg. No. 53,757).and Chien Wei Chou (Reg. No. 41,672).

Please address all correspondence and telephone calls regarding this application to:

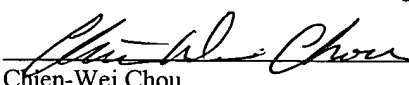
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The undersigned is the representative for the Assignee of the entire right, title, and interest in the patent application identified above. A copy of the assignment or other documents in the chain of title are attached.

The undersigned (whose title is supplied below) is authorized to act on behalf of the Assignee.

Taiwan Semiconductor Manufacturing, Inc.

Date


Chien-Wei Chou